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Kind regards,

Team Nexperia

# PEMB16; PUMB16

PNP/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = 47 k $\Omega$ 

Rev. 03 — 31 August 2009

**Product data sheet** 

### 1. Product profile

### 1.1 General description

PNP/PNP resistor-equipped transistors

Table 1. Product overview

Type number	ype number Package		NPN/PNP	NPN/NPN
	NXP	JEITA	complement	complement
PEMB16	SOT666	-	PEMD16	PEMH16
PUMB16	SOT363	SC-88	PUMD16	PUMH16

#### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	$k\Omega$
R2/R1	bias resistor ratio		1.7	2.1	2.6	



## 2. Pinning information

Table 3. Pinning

Table 5.	ı ıııılıy		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6   5   4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1 1 2 3
			006aaa212

## 3. Ordering information

Table 4. Ordering information

Type number	Package				
	Name	Description	Version		
PEMB16	-	plastic surface mounted package; 6 leads	SOT666		
PUMB16	SC-88	plastic surface mounted package; 6 leads	SOT363		

# 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMB16	5G
PUMB16	B*7

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

### 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	-50	V
$V_{CEO}$	collector-emitter voltage	open base	-	-50	V
$V_{EBO}$	emitter-base voltage	open collector	-	-5	V
V <sub>I</sub>	input voltage				
	positive		-	+7	V
	negative		-	-40	V
lo	output current		-	-100	mA
I <sub>CM</sub>	peak collector current		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT363		<u>[1]</u> _	200	mW
	SOT666		[1] [2] _	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1] [2]	300	mW

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C				
	SOT363		<u>[1]</u> _	-	625	K/W
	SOT666		[1] [2]	-	625	K/W
Per device	•					
$R_{th(j-a)}$	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1] [2] _	-	416	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

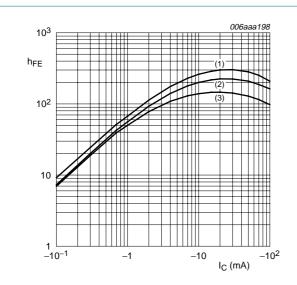
<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

### 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	-1	μΑ
	cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-120	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-0.8	-0.5	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -2 \text{ mA}$	-2	-1.1	-	V
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF



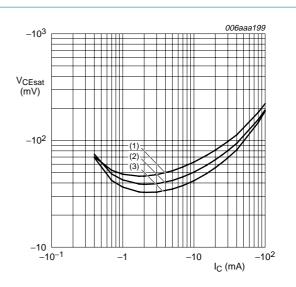
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 1. DC current gain as a function of collector current; typical values



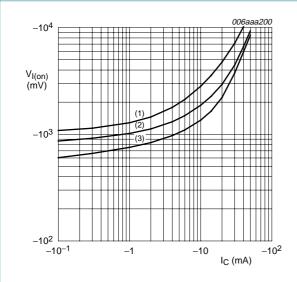
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



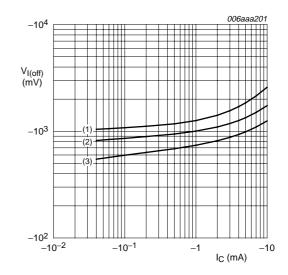


(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 3. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

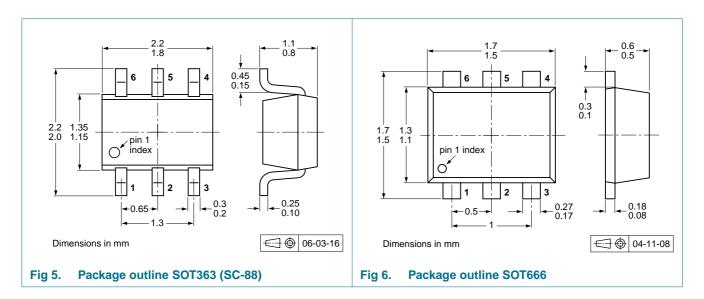
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 4. Off-state input voltage as a function of collector current; typical values

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## 8. Package outline



## 9. Packing information

### Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description		Packing qua	ntity	
				3000	4000	10000
PEMB16	SOT666	4 mm pitch, 8 mm tape and reel;		-	-115	-
PUMB16	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-135
PUMB16	SOT363	4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

# 10. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PEMB16_PUMB16_3	20090831	Product data sheet	-	PEMB16_PUMB16_2	
Modifications:	<ul> <li>This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.</li> <li>Figure 5 "Package outline SOT363 (SC-88)": updated</li> </ul>				
PEMB16_PUMB16_2	20050610	Product data sheet	-	PUMB16_1	
PUMB16_1	20031103	Product specification	-	-	

### 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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